



# CHARACTERISATION OF SINGLE-DIODE SILICON SENSORS FOR THE CMS HGICAL PROJECT

Jenan Amer

Supervisors: Leena Diehl,  
Oliwia Kałuzińska

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# *Who Am I?*

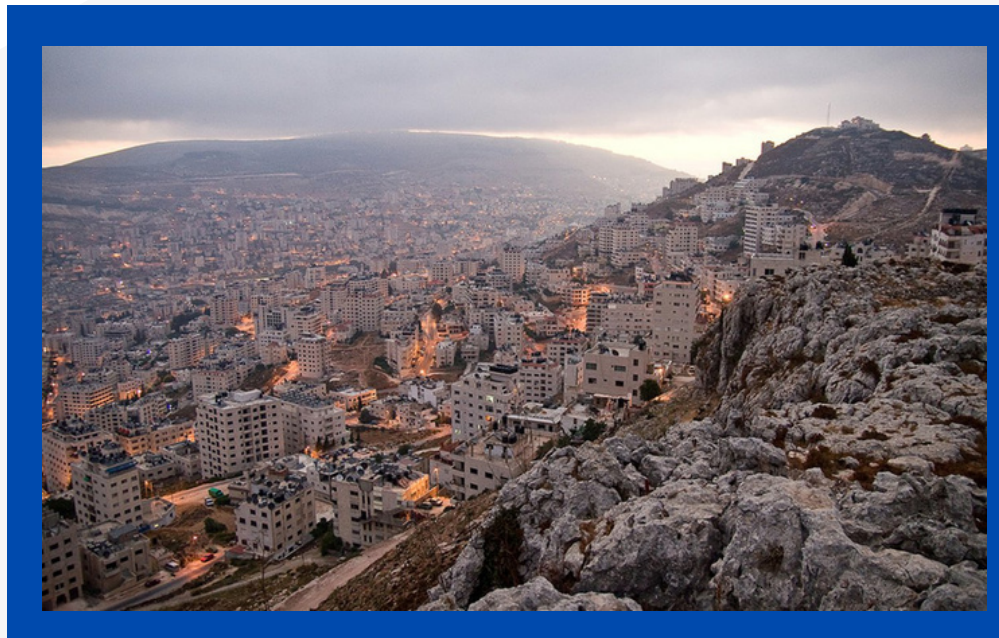
**Jenan Amer**

Bachelor in physics, An Najah National university, Palestine



**Mas-ha, Salfit**

**Nablus city**



**An Najah National University**



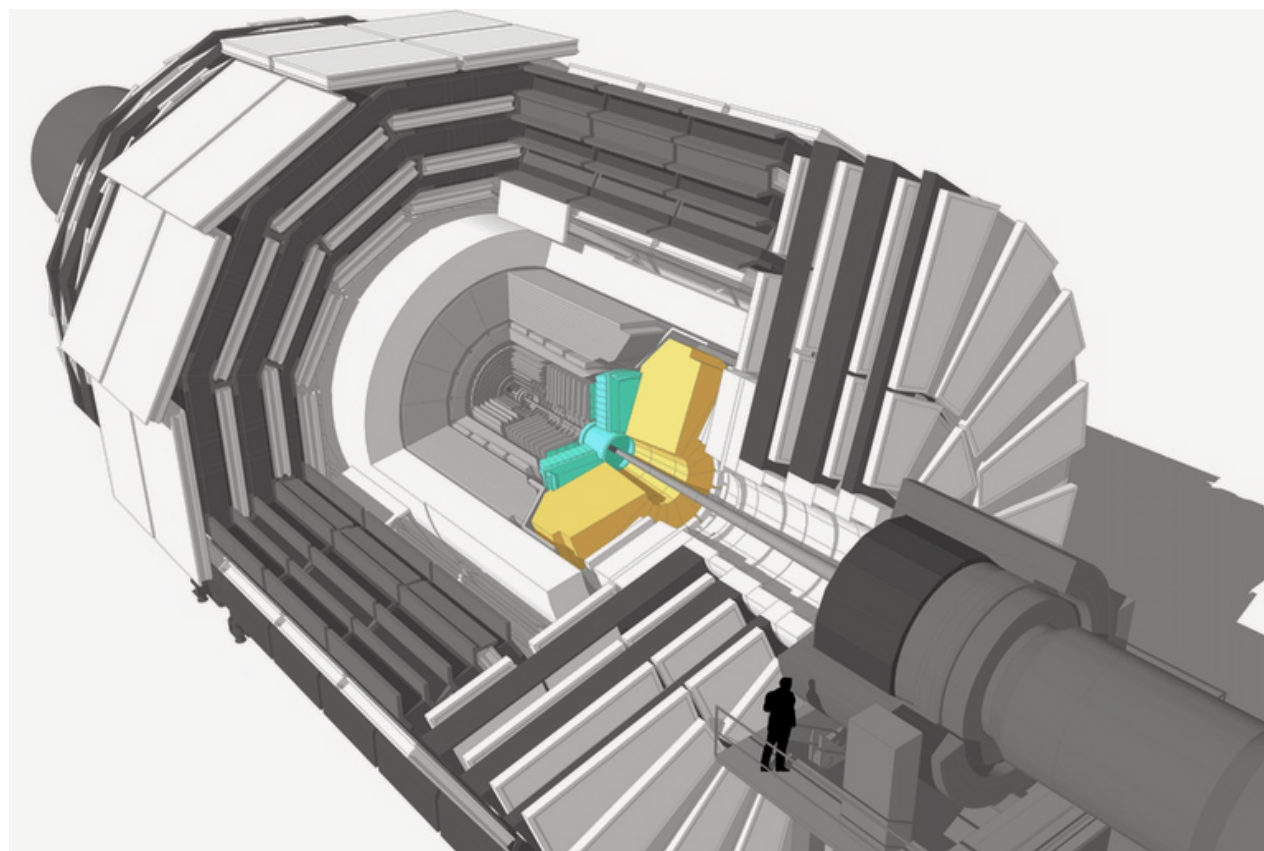
# OUTLINE

- Introduction.
  - The LHC upgrade and CMS.
  - What is HGICAL?
- My Work
  - Silicon sensors.
  - Electrical characterization of single diodes.
  - Results.
- Conclusion and ongoing work.





# THE LHC UPGRADE AND OUR MOTIVATION



## What is HGCAL?

HGCAL will use  $\sim 620 \text{ m}^2$  silicon sensors produced on 8-inch wafers.

Three different thicknesses:

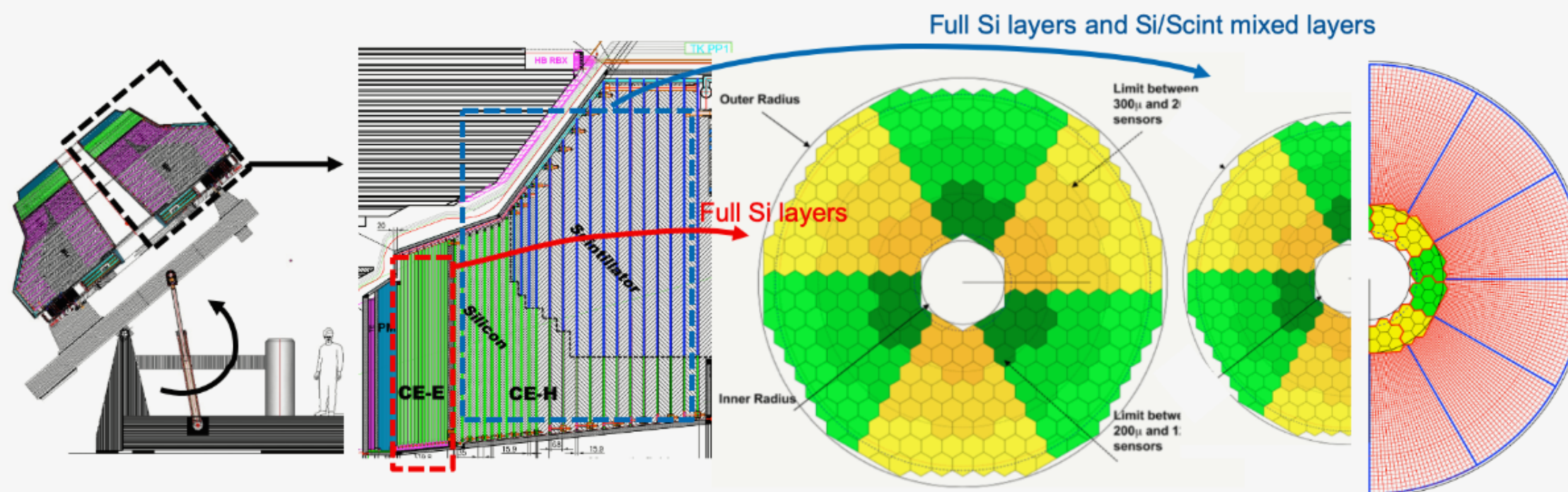
$300 \mu\text{m}$ ,  $200 \mu\text{m}$  (Float zone) and  $120 \mu\text{m}$  (Epitaxial).

Fluences of up to  $1\text{e}16 \text{ neq}/\text{cm}^2$

CMS is a general purpose detector.

LHC  $\rightarrow$  HL-LHC  $\sim 200$  pileups per bunch crossing.

CMS Endcap Calorimeter will be replaced by the High Granularity Calorimeter (HGCAL) for the HL-LHC





# *WHY SILICON SENSORS?*

Radiation  
hardness

High readout  
speed

Possibility of  
integrating detector  
and readout  
electronics on a  
common substrate

Extremely  
precise position  
measurement

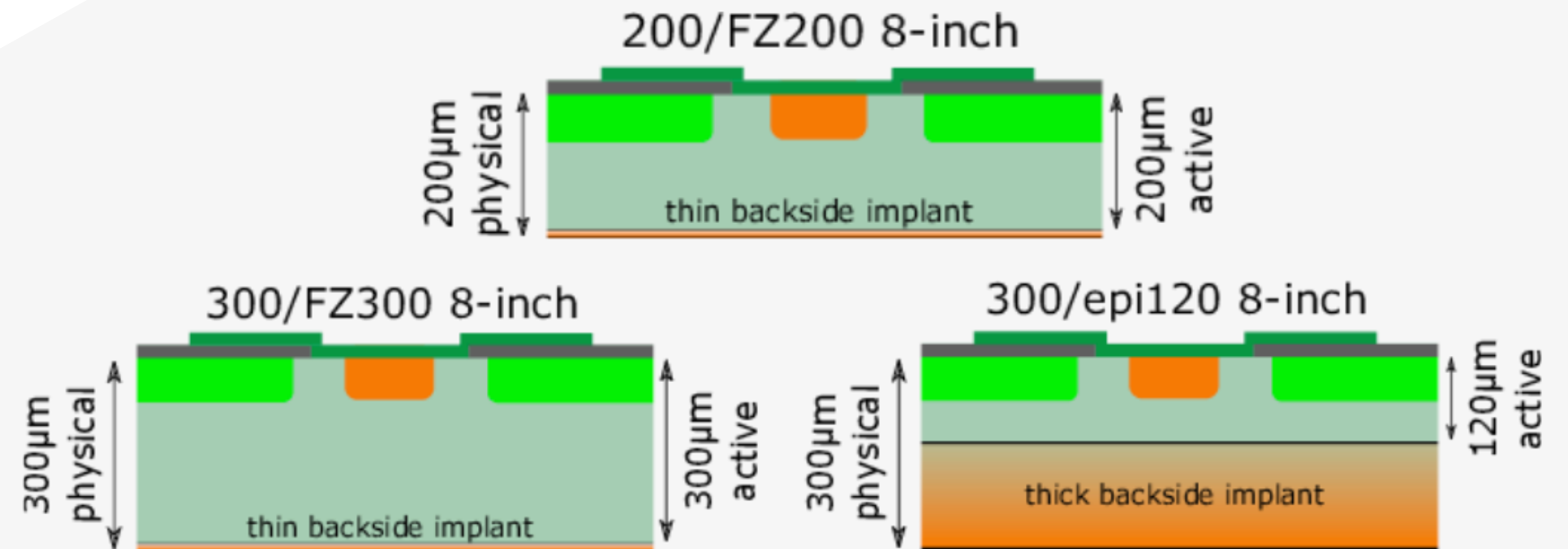
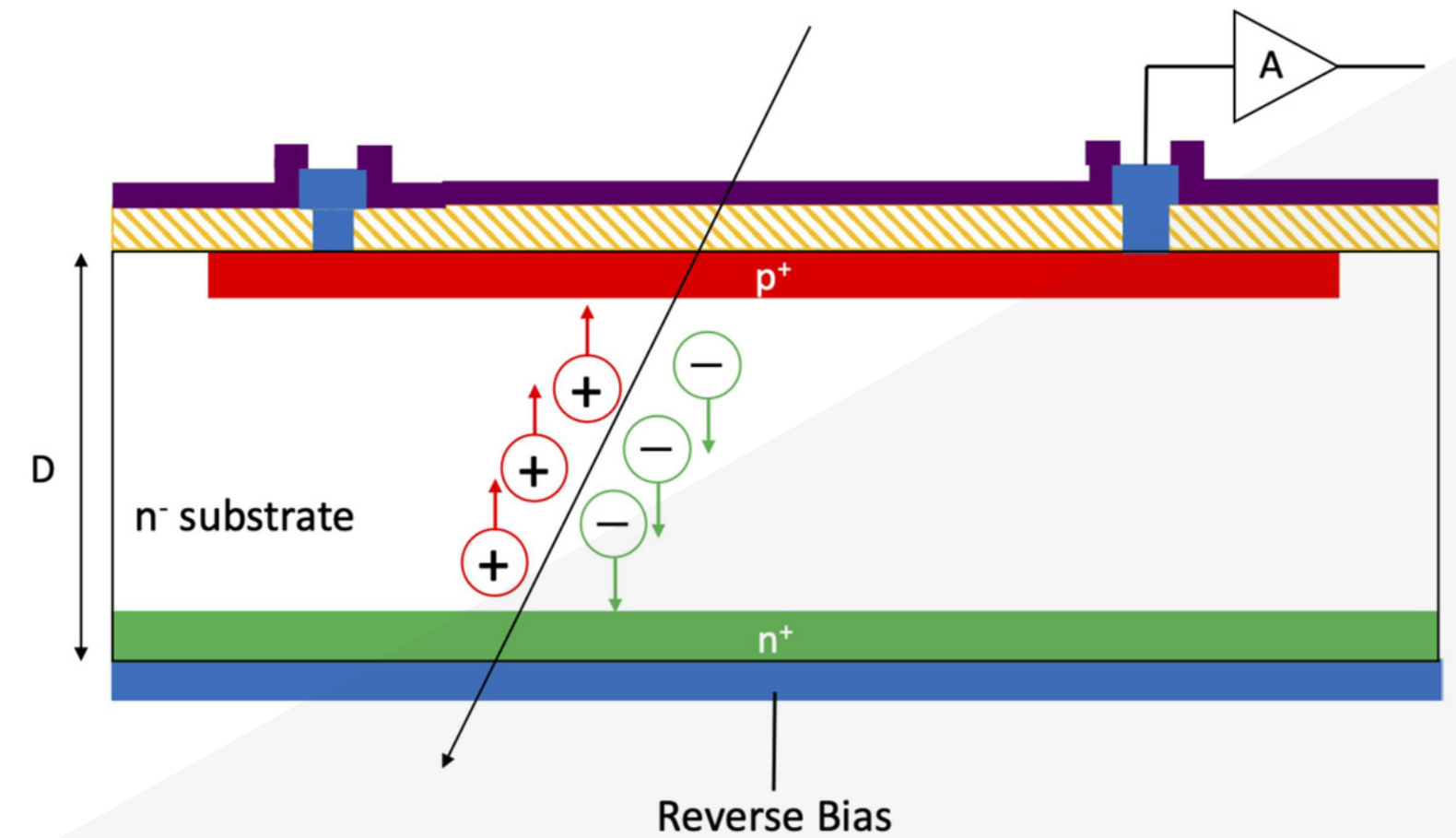
Simultaneous  
measurement of  
energy, position  
and arrival time





# HOW SILICON SENSORS WORK?

- Charged particles traversing the detector create electron-hole pairs.
- The electron-hole pairs are separated by an electric field and drift to the electrodes. This is the signal we are looking for.



Sensors cross section (not to scale):

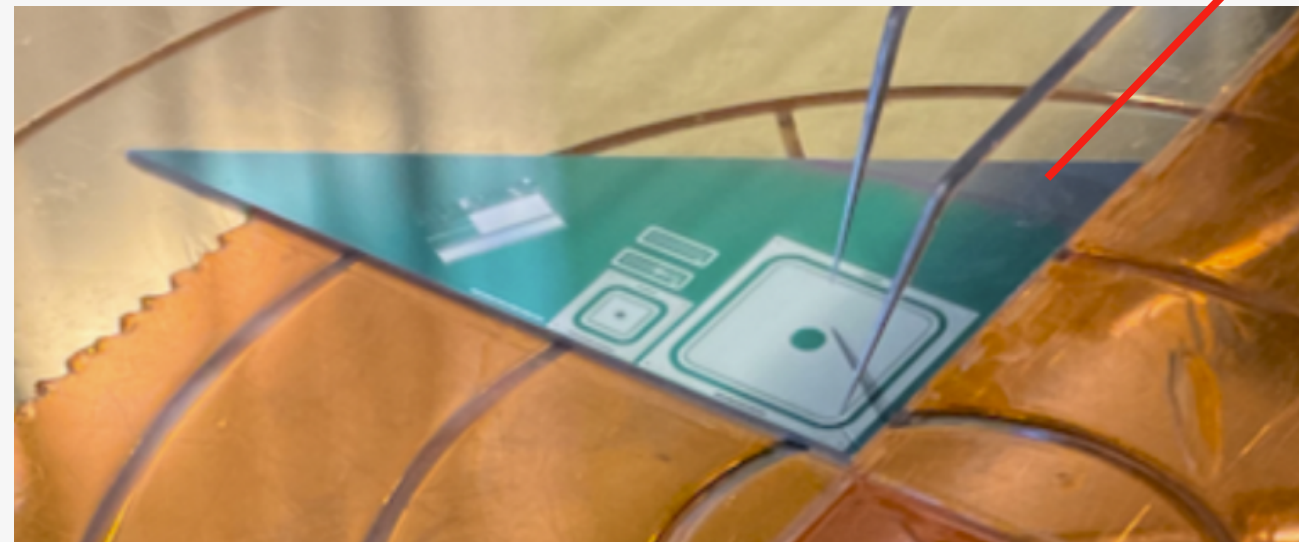
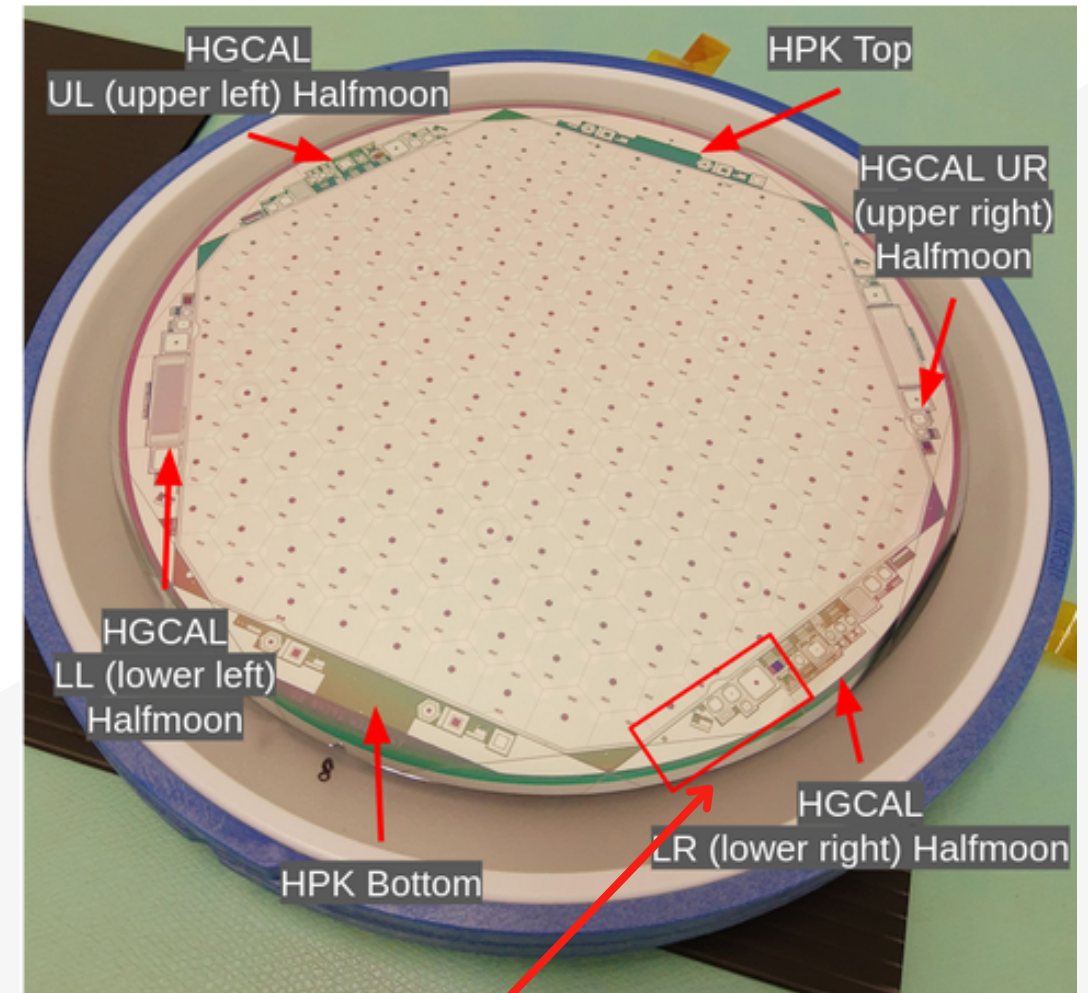
300, 200 and 120  $\mu\text{m}$ ; FZ denotes float zone process and epi – epitaxial process





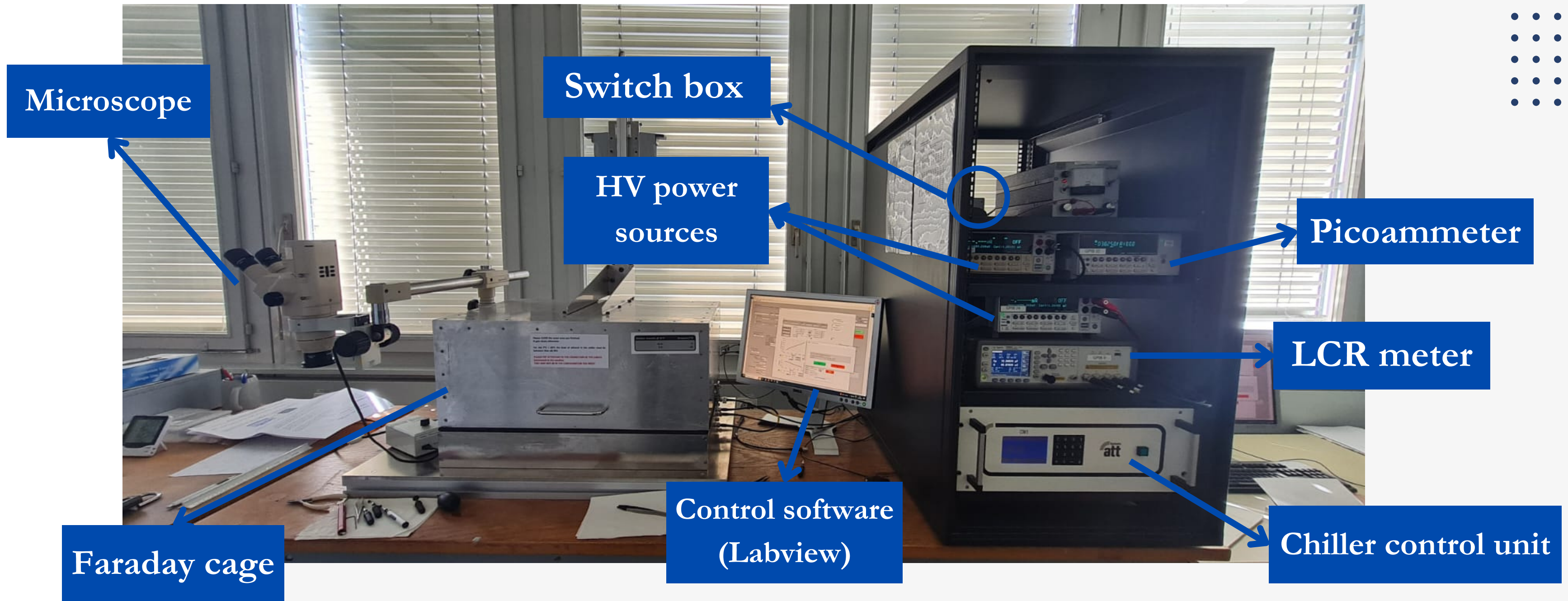
# *FULL SENSORS AND DIODE TEST STRUCTURES*

- Circular wafers are cut into Hexagonal full sensors.
- Remaining space is used for the small diode test structures.
- Set of pre-series and pre-production diodes were irradiated at JSI (Jozef Stefan Institute) in June 2023
- Electrical characterization through CV/IV measurements is performed on the diodes.





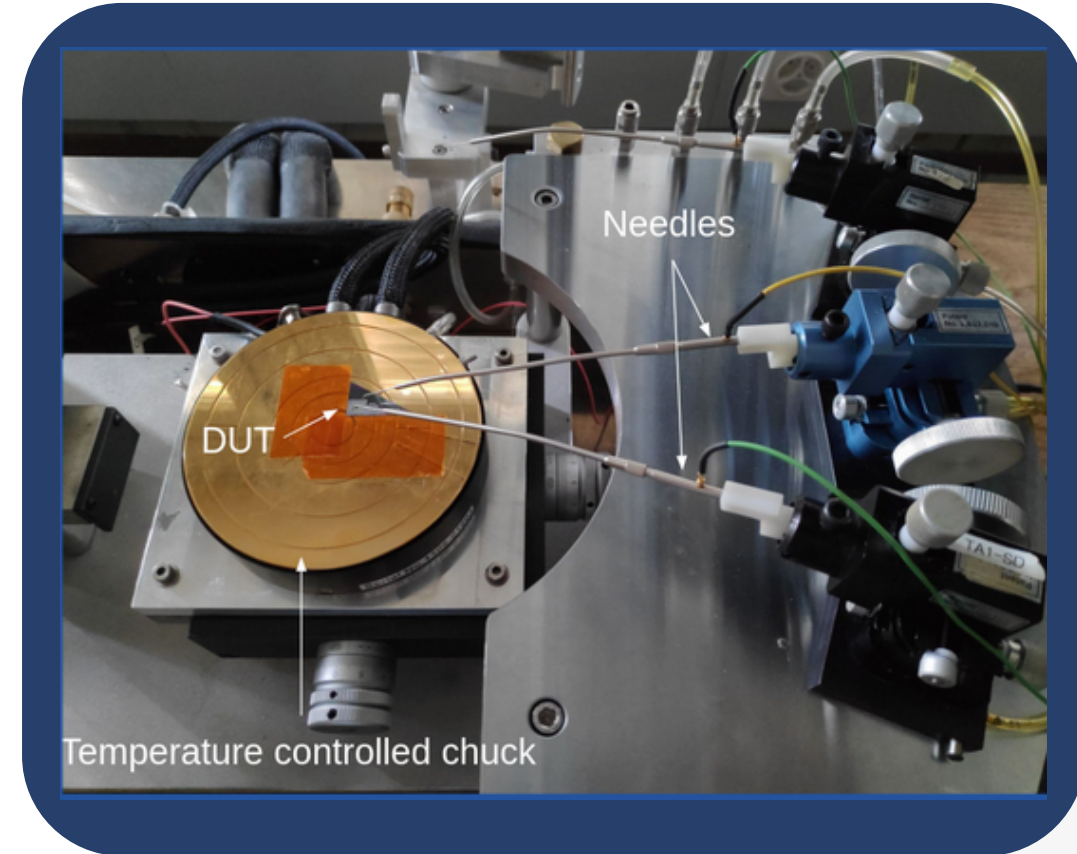
# SETUP



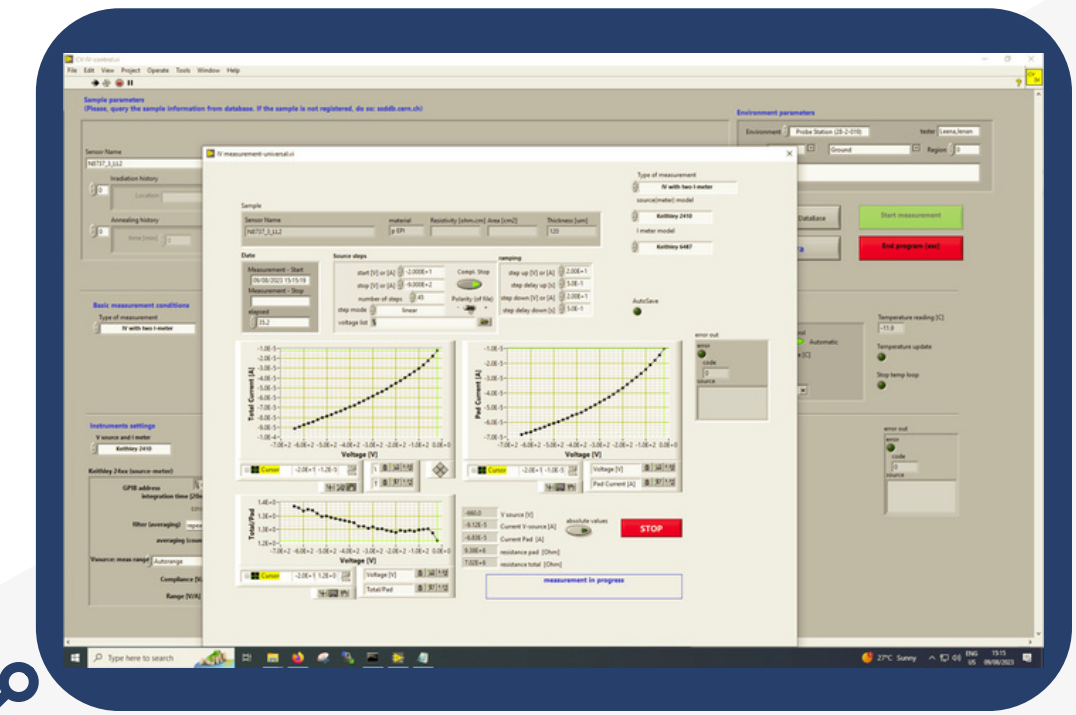
CERN EP-DT-DD SSD group IVCV probestation



# ELECTRICAL CHARACTERIZATION PROCESS



CV and IV Measurements done on a temperature controlled chuck



Measurements controlled by Labview

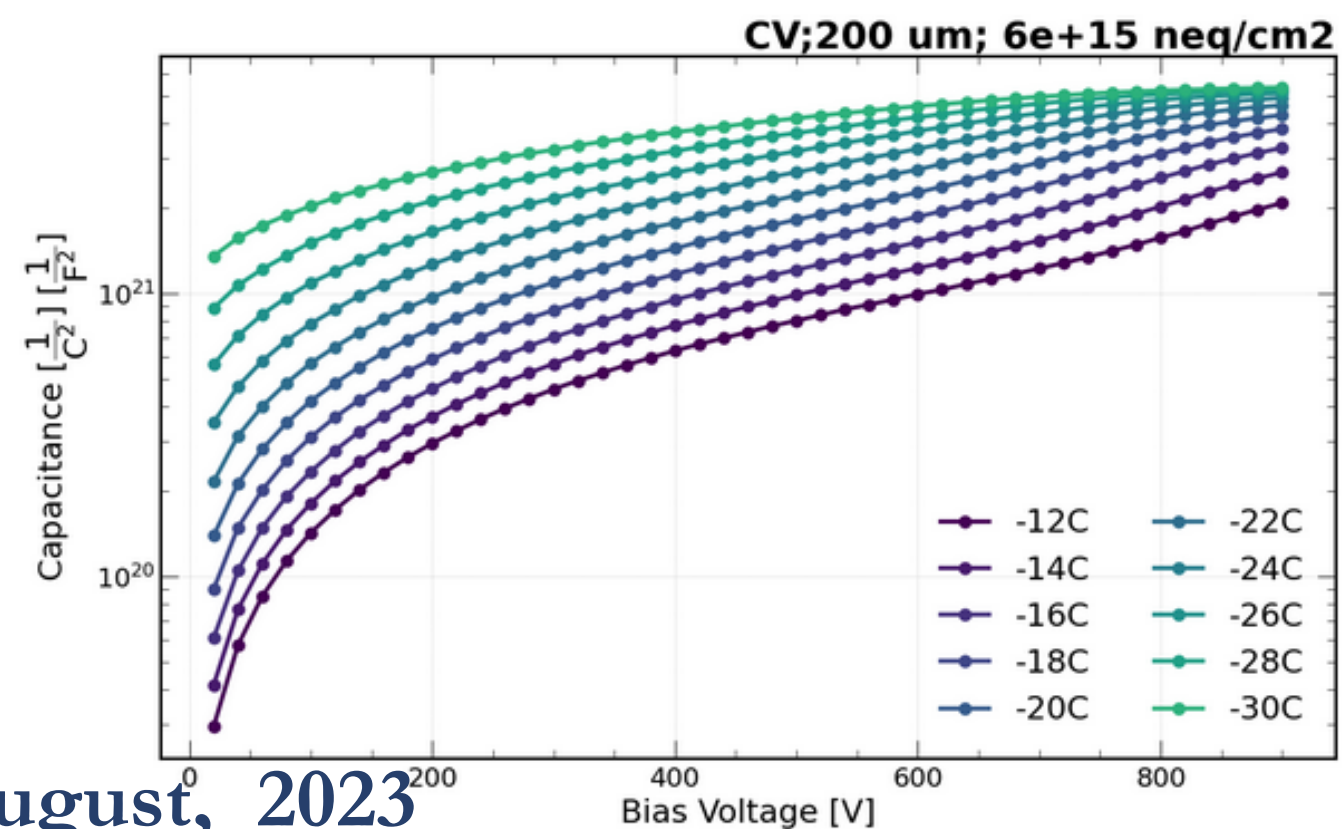
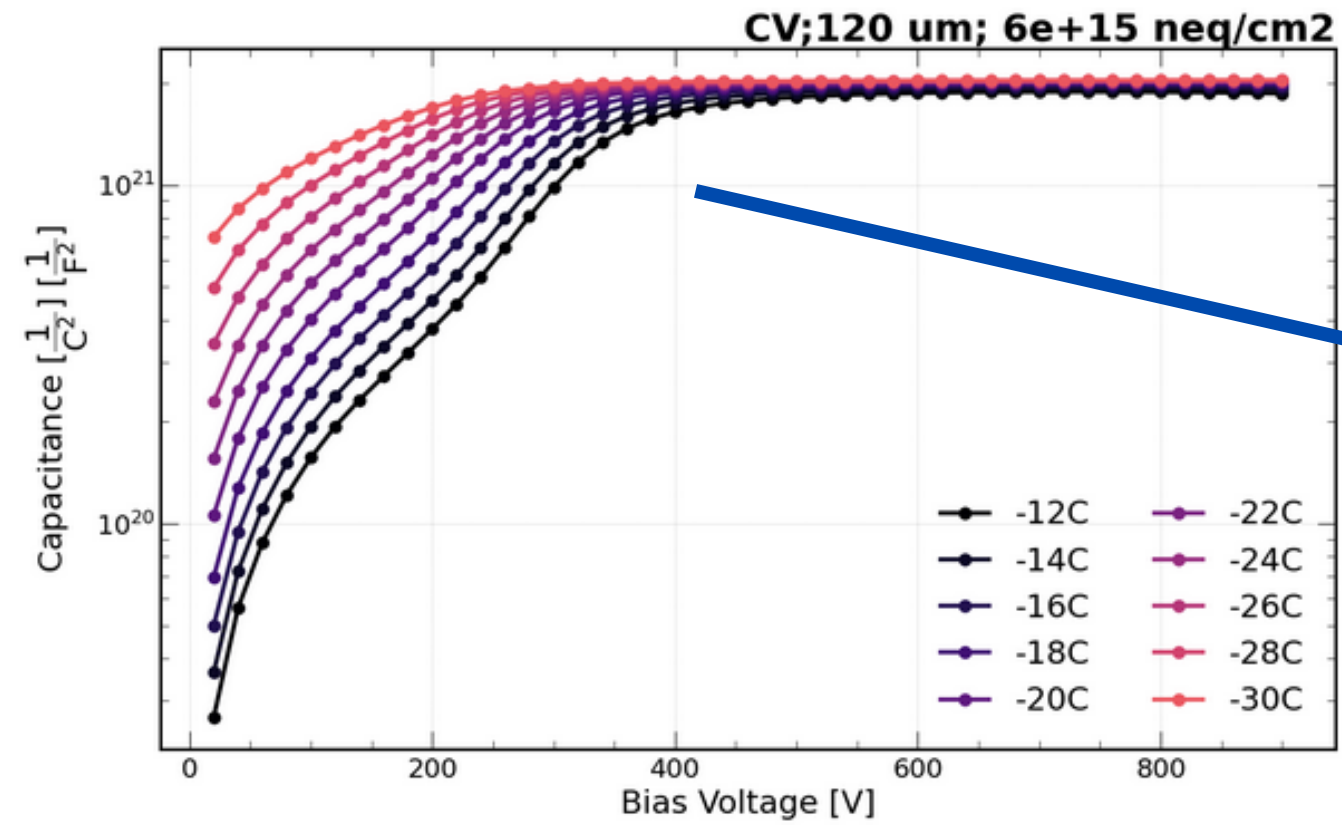
Inside the Faraday cage is where the test area is



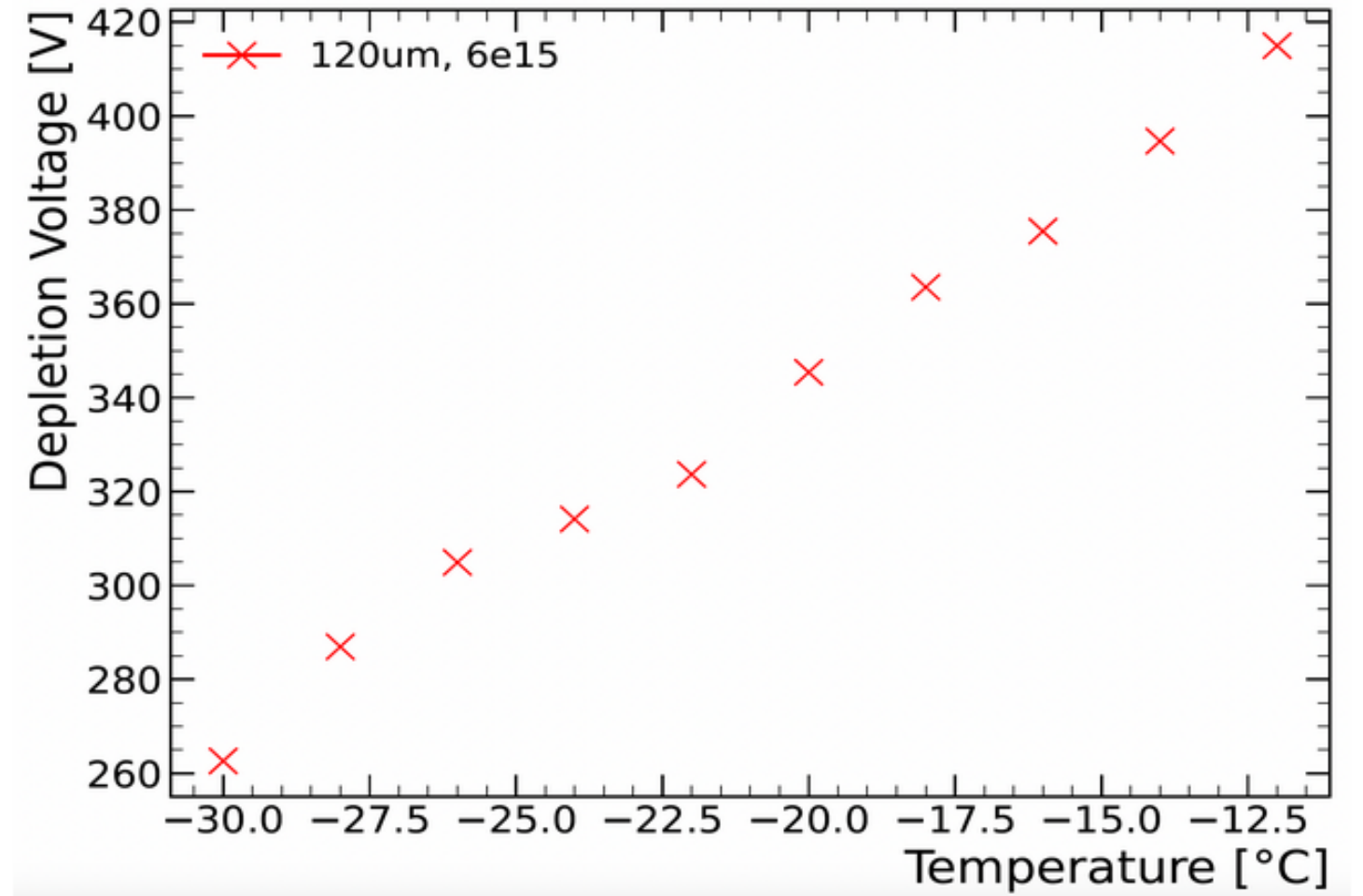
Contact is done with the DUT at the pad and at the guard ring



# CV temperature Scans



The behavior of the depletion voltage with temperature

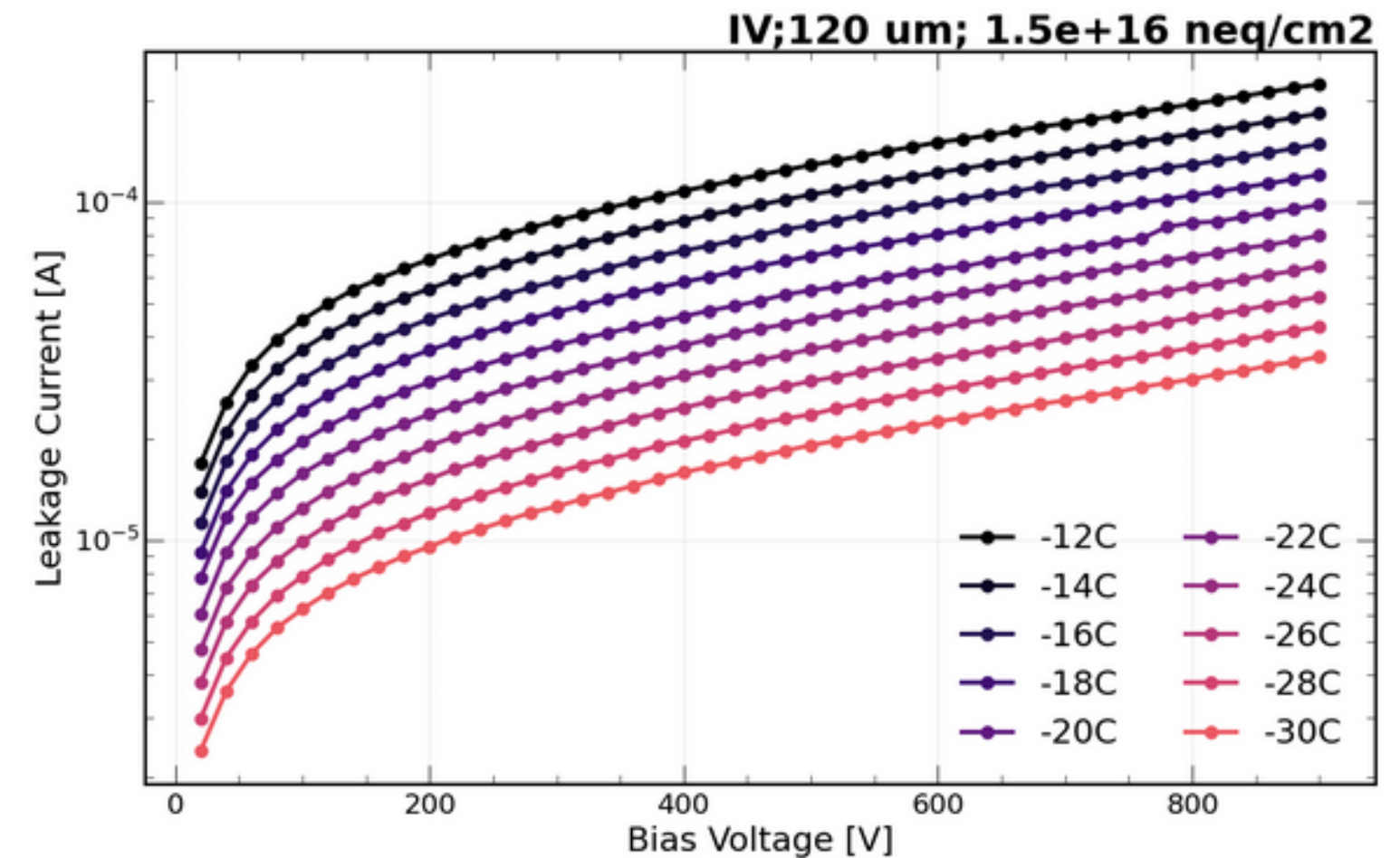
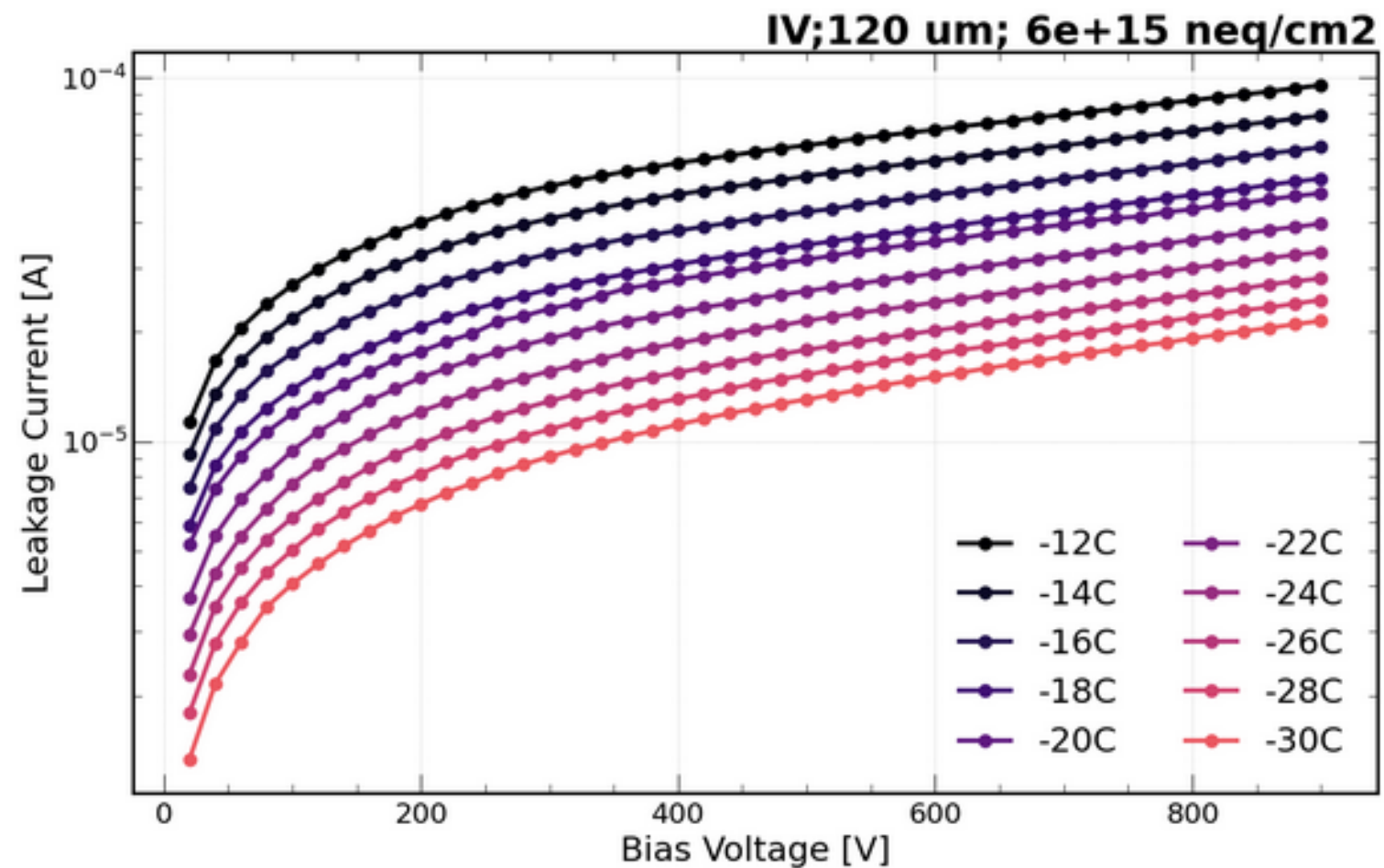


Temperature increase → depletion voltage increase

Diodes with higher thickness don't reach full depletion until applied voltage of 900V



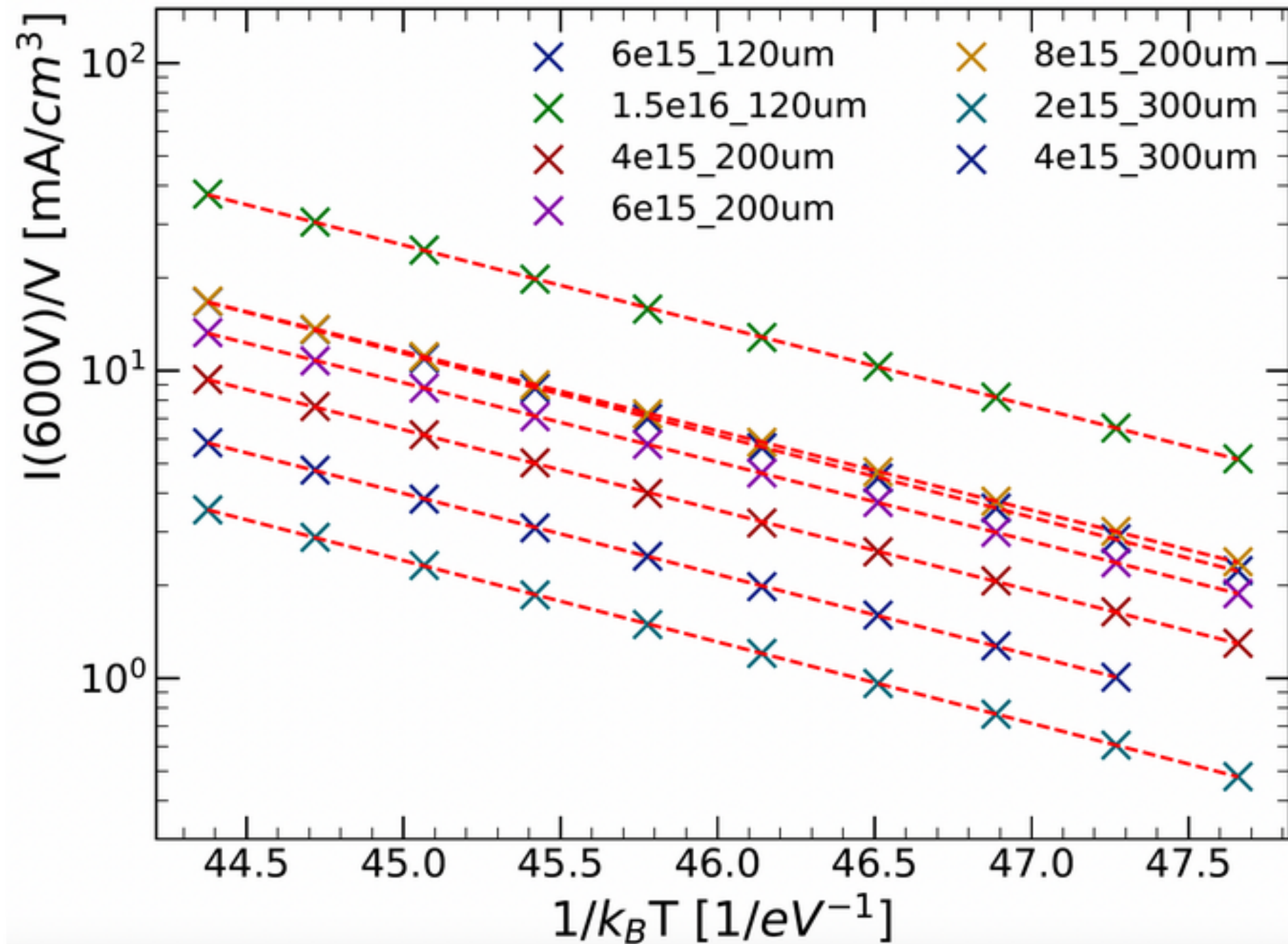
# *IV temperature scans*



- For the same thickness of diodes the leakage current increases for higher fluences.
- The value of the leakage current also increases exponentially for the irradiated diodes as the temperature is increased.



# Arrhenius plot



$$\frac{I(600V)}{V} = \exp\left(\frac{-A}{K_B T} + B\right)$$

Activation energy

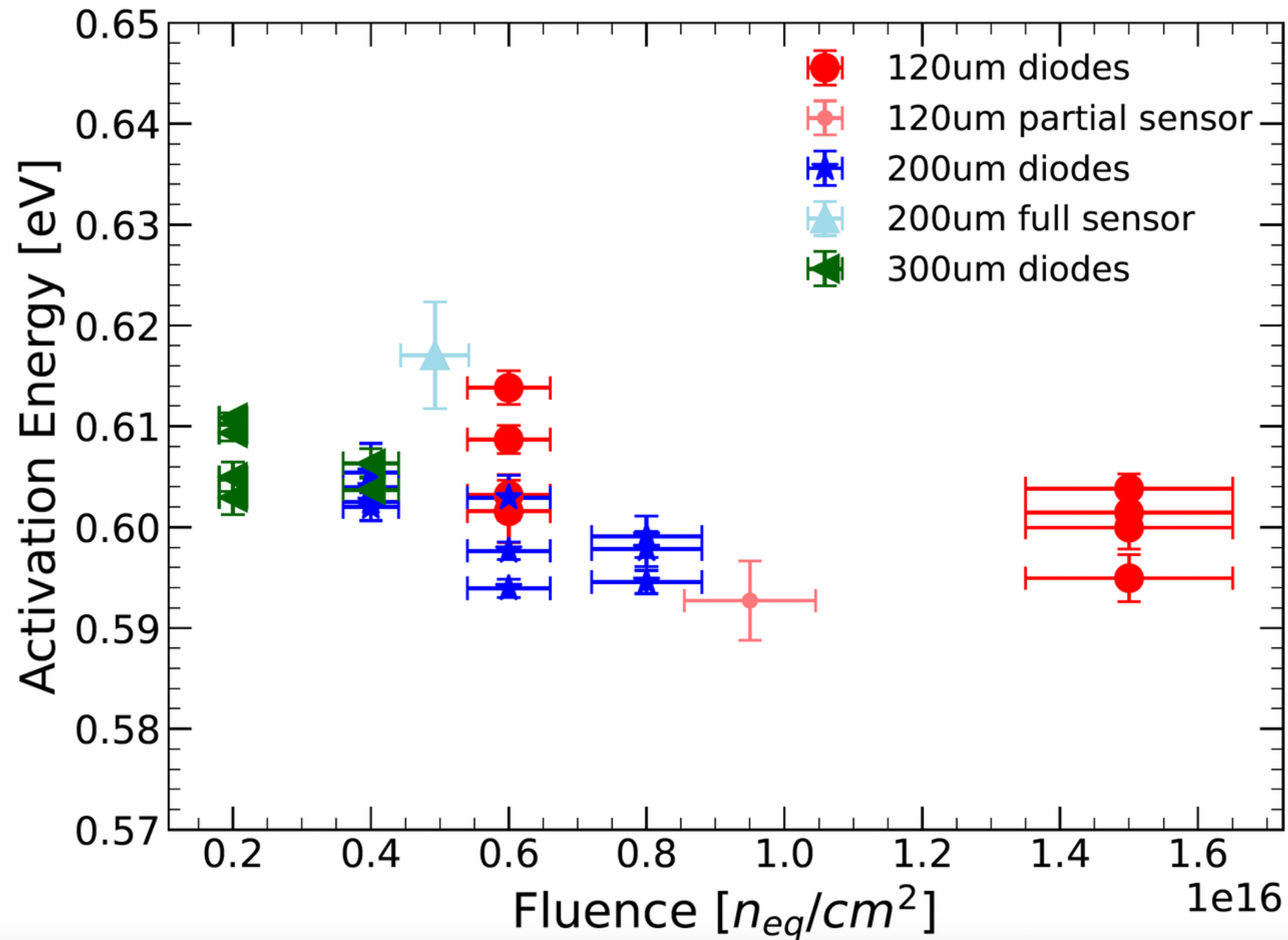
We have roughly same slope for all measurements.

Different values for the same fluence if the thicknesses vary.

Offset between thicknesses is constant (see 4e15)



# *Activation energy vs the Fluence*



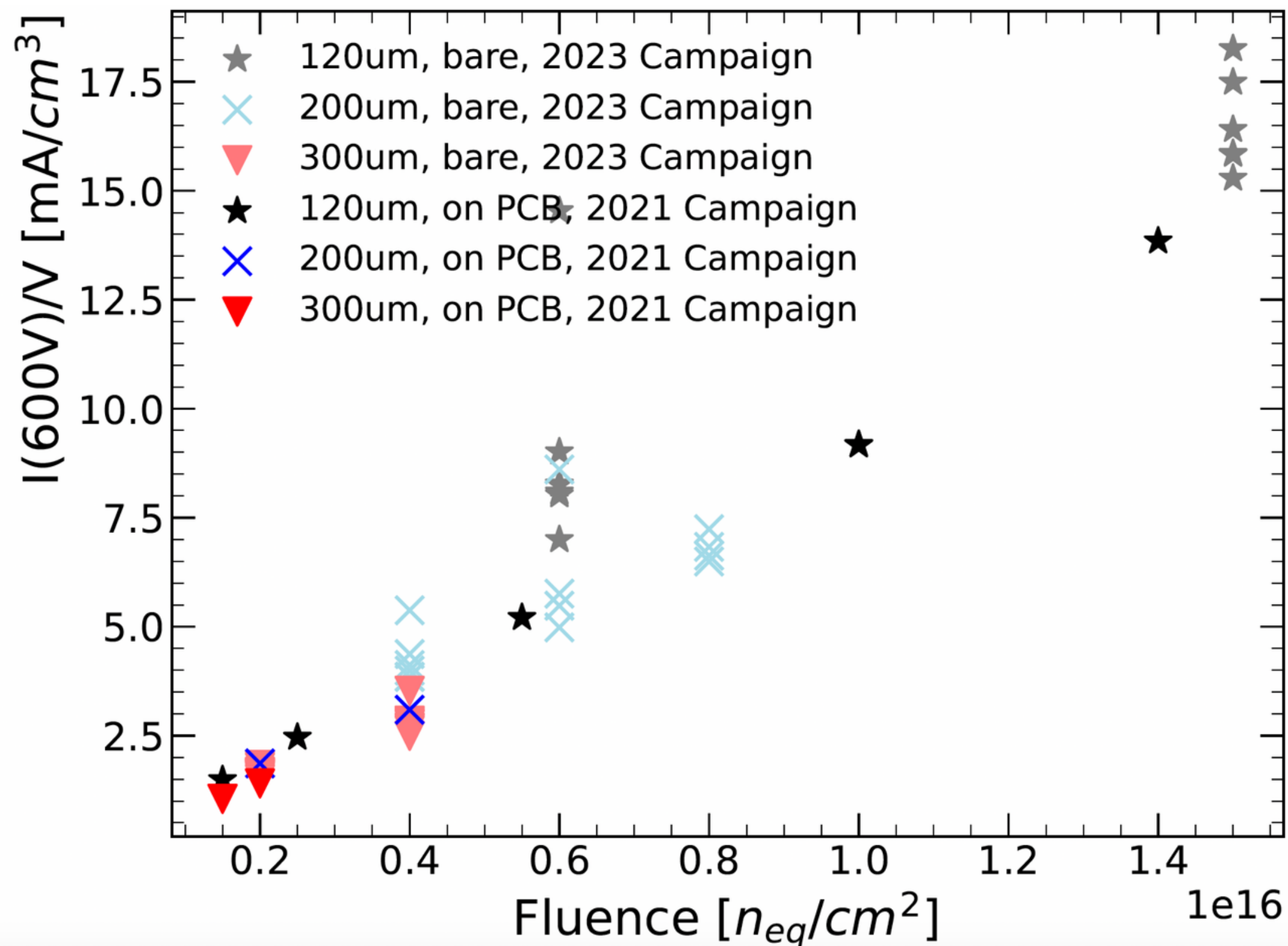
Offset between thickness

Slight fluence dependence possible

We are still investigating this possible dependence by increasing the sample of sensors tested.



# *I<sub>leak</sub>/V vs fluence (alpha plot)*



We have large spread for the new sensors compared to previous campaigns.

A slight difference between thicknesses for the same fluence was also observed with the old sensors

$$\frac{I}{V} = \alpha \cdot \phi$$



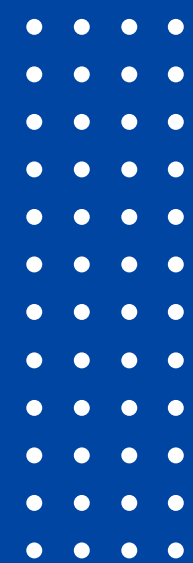
# Conclusion

- Temperature studies were performed on seven diodes of different thicknesses and fluences.
- Results are in agreement with what we expected:
  - Exponential increase of current with temperature.
  - Shift of depletion voltage with temperature in CV measurements.

# Ongoing work

Investigation of possible fluence dependencies in the activation energy, investigation of the larger spread in the alpha plot.





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# THANK YOU

*Any questions?*

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